



40V 150°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
40V	7.5 m Ω @ $V_{GS} = 10$ V	49.1A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions
- DC-DC Converters

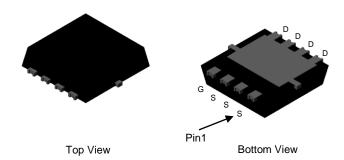
Features and Benefits

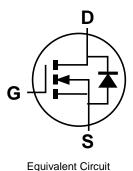
- Excellent Q_{GD} x R_{DS(ON)} Product (FOM)
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- 100% Unclamped Inductive Switching, Test in Production Ensures More Reliable and Robust End Application
- Wettable Flank for Improved Optical Inspection
 - Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMT47M2SFVWQ</u>)

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (Approximate)

PowerDI3333-8 (SWP) (Type UX)





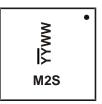
Ordering Information (Note 4)

Part Number	Case	Packaging		
DMT47M2SFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel		
DMT47M2SFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\frac{\text{M2S} = \text{Product Type Marking Code}}{\frac{\text{YY}}{\text{WW}} = \text{Date Code Marking}}$ $\frac{\text{YY}}{\text{YY}} = \text{Last Two Digits of Year (ex: 19 = 2019)}$ WW = Week Code (01 to 53)



Maximum Ratings (@T_A =+ 25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	40	V	
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6), V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	Ι _D	49.1 39.2	А
Continuous Drain Current (Note 5), V _{GS} = 10V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	15.4 12.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	196	А	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	30.8	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1	I _{SM}	196	Α	
Avalanche Current, L = 0.1mH	I _{AS}	24.7	Α	
Avalanche Energy, L = 0.1mH	Eas	30.5	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Γ _A = +25°C	P_{D}	2.67	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	46.5	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P_{D}	27.1	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	4.61	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	2.5	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	5.9	7.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V_{SD}		0.88	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	897	_		V_{DS} = 20V, V_{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	530	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	12.4	_			
Gate Resistance	Rg	_	2.07	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	12.1	_		V _{DS} = 20V, I _D = 20A, V _{GS} = 10V	
Gate-Source Charge	Qgs	_	2.0	_	nC		
Gate-Drain Charge	Q _{gd}	_	1.9	_			
Turn-On Delay Time	t _{D(ON)}	_	5.36	_		$V_{DD} = 20V, V_{GS} = 10V,$ $R_G = 3\Omega, I_D = 20A$	
Turn-On Rise Time	t _R	_	4.54	_	20		
Turn-Off Delay Time	t _{D(OFF)}	_	12.1	_	ns		
Turn-Off Fall Time	t _F	_	5.59	_			
Body Diode Reverse Recovery Time	t _{RR}	_	39.1	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	53.3	_	nC	$I_F = 20A$, di/dt = 100A/ μ s	

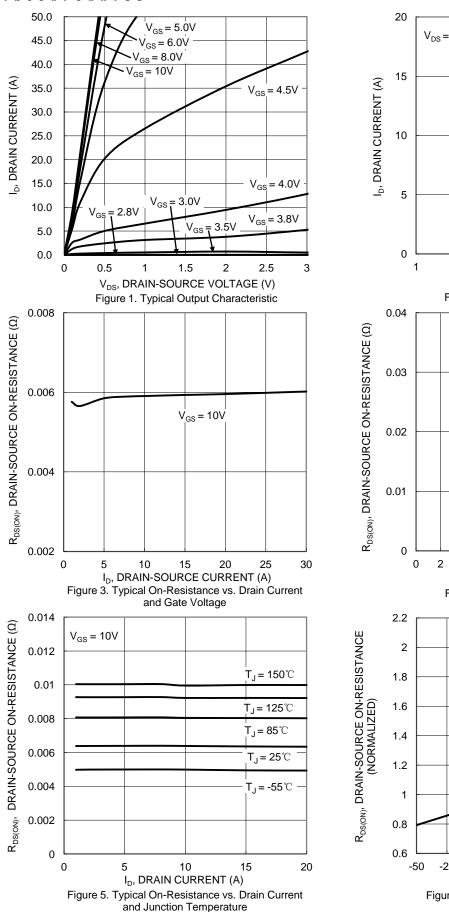
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate. Notes:

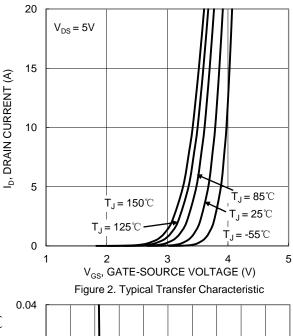
^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).

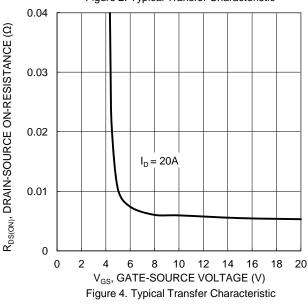
^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.











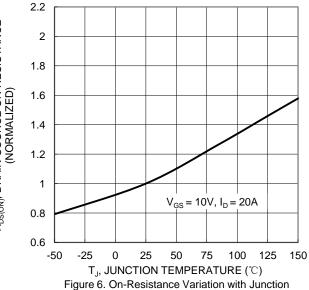


Figure 6. On-Resistance Variation with Junction Temperature



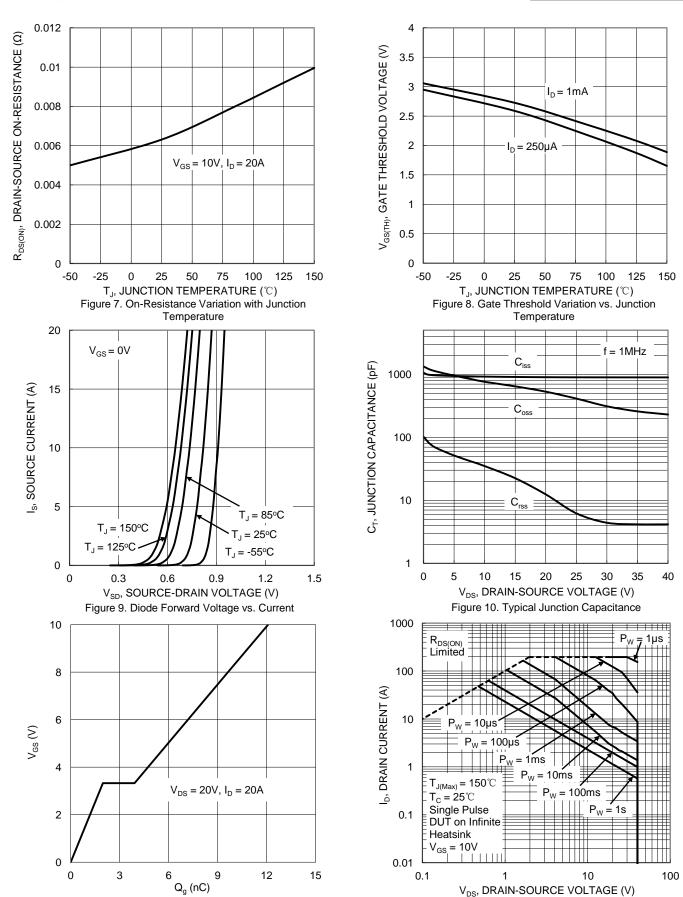


Figure 11. Gate Charge

Figure 12. SOA, Safe Operation Area



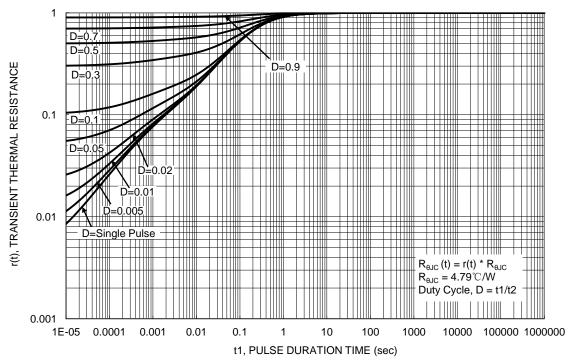


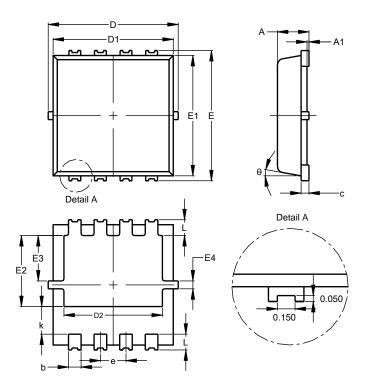
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

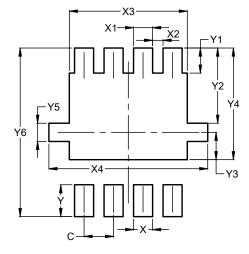


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	_	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Value (in mm)			
0.650			
0.420			
0.420			
0.230			
2.600 3.500			
0.550			
1.650			
0.600			
2.450			
0.400			
3.700			

Dimensional Wales (in



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